

Switchmode Dual Ultrafast Power Rectifiers

Designed for use in switching power supplies, inverters and as free- wheeling diodes. These state-of-the-art devices have the following

Features

- *High Surge Capacity
- *Low Power Loss, High efficiency
- *Glass Passivated chip junctions
- *150°C Operating Junction Temperature
- *Low Stored Charge Majority Carrier Conduction
- *Low Forward Voltage, High Current Capability
- *High-Switching Speed 35 Nanosecond Recovery Time
- * Plastic Material used Carries Underwriters Laboratory Flammability Classification 94V-O
- * Ph free
- *In compliance with EU RoHs directives





MAXIMUM RATINGS

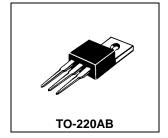
Characteristic	Symbol	U20C20C	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	200	V
RMS Reverse Voltage	V _{R(RMS)}	140	V
Average Rectifier Forward Current Total Device (Rated V _R)	I _{F(AV)}	10 20	А
Peak Repetitive Forward Current (Rate V _R , Square Wave, 20kHz)	I _{FM}	20	А
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions half-wave, single phase, 60Hz)	I _{FSM}	200	А
Operating and Storage Junction Temperature Range	T_J , T_stg	-65 to +150	$^{\circ}\!\mathbb{C}$

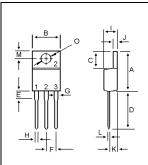
ELECTRICAL CHARACTERISTICS

Characteristic	Cumple of	N disa		Max	I India
Characteristic	Symbol	Min.	Тур.	Max.	Unit
Maximum Instantaneous Forward Voltage					
$(I_F = 10 \text{ Amp T}_C = 25^{\circ}C)$	V_{F}		0.91	0.975	V
(I _F =10 Amp T _C = 125°C)			0.78		
Maximum Instantaneous Reverse Current					
(Rated DC Voltage, T _C = 25°C)	I _R		0.01	10	uA
(Rated DC Voltage, T _C = 125°C)			5		
Reverse Recovery Time ($I_F = 0.5 \text{ A}$, $I_R = 1.0$, $I_{rr} = 0.25 \text{ A}$)	T _{rr}		17	35	ns
Typical Thermal Resistance junction to case	$R_{\theta jc}$		3.4		°C/w
Typical Junction Capacitance (Reverse Voltage of 4 volts & f=1 MHz)	СР		65		₽F

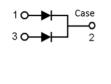
ULTRA FAST RECTIFIERS

20 AMPERES 200 VOLTS

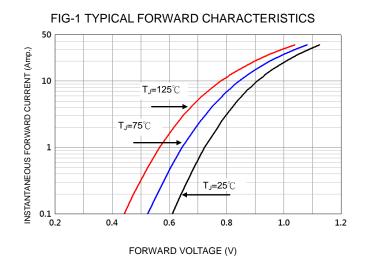


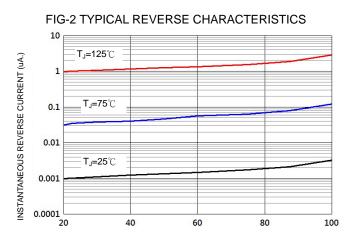


DIM	MILLIMETERS			
DIIVI	MIN	MAX		
Α	14.68	16.00		
В	9.78	10.42		
С	5.02	6.60		
D	13.00	14.62		
E	3.10	4.19		
F	2.41	2.67		
G	1.10	1.67		
Н	0.69	1.01		
ı	4.22	4.98		
J	1.14	1.40		
K	2.20	3.30		
L	0.28	0.61		
М	2.48	3.00		
0	3.50	4.00		

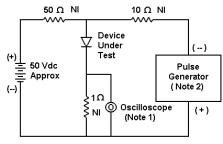












Notes:

- 1. Rise Time = 7 ns max. Input Impedance = 1 M Ω , 22 pF
- 2. Rise Time = 10 ns max. Input Impedance = 50 Ω

FIG-3 FORWARD CURRENT DERATING CURVE 20 16 12 8

AVERAGE FORWARD RECTIFIED CURRENT (Amp.)

0 L

25

$\mbox{LEAD TEMPERATURE ($^{\circ}$)} \label{eq:constraint}$ FIG-4TYPICAL JUNCTION CAPACITANCE

75

100

125

150

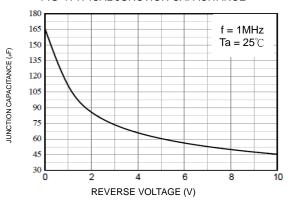
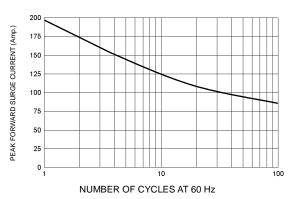
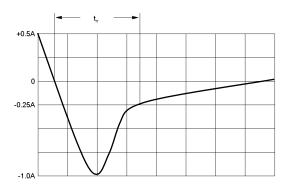


FIG-5PEAK FORWARD SURGE CURRENT





Set time base for 10/20 ns/cm

FIG-6 Reverse Recovery Time Characteristic and Test Circuit Diagram